



# GaAs PHEMT MMIC LOW NOISE AMPLIFIER, 13 - 25 GHz

#### Typical Applications

The HMC342LC4 is ideal for:

- Point-to-Point Radios
- Point-to-Multi-Point Radios & VSAT
- Test Equipment & Sensors
- Military End-Use

#### **Features**

Noise Figure: 3.5 dB

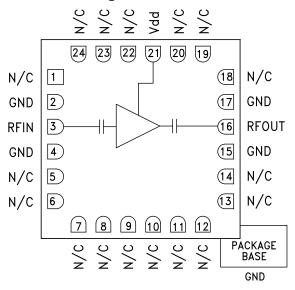
Gain: 22 dB

Single Positive Supply: +3V @ 43 mA

50 Ohm Matched Input/Output

RoHS Compliant 4x4 mm SMT Package

#### **Functional Diagram**



#### **General Description**

The HMC342LC4 is a GaAs pHEMT MMIC Low Noise Amplifier housed in a leadless 4x4 mm RoHS compliant SMT package. Operating from 13 to 25 GHz, the amplifier provides 22 dB of gain and +19 dBm of output IP3 from a single +3V supply. The low noise figure performance of 3.5 dB is ideal for receive and transmit pre-driver applications. The RF I/Os are DC blocked and matched to 50 Ohms for ease of use. The HMC342LC4 allows the use of surface mount manufacturing techniques and requires no external matching components.

## Electrical Specifications, $T_A = +25^{\circ}$ C, Vdd = +3V, Idd = 43 mA

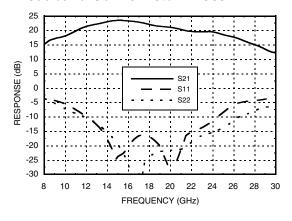
Parameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Frequency Range	13 - 18		18 - 22		22 - 25		GHz			
Gain	19	22		17	20		16	19		dB
Gain Variation Over Temperature		0.025	0.035		0.025	0.035		0.025	0.035	dB/ °C
Noise Figure		3.5	4.0		3.5	4.0		3.5	4.5	dB
Input Return Loss		15			15			10		dB
Output Return Loss		15			20			15		dB
Output Power for 1 dB Compression (P1dB)		7			8			9		dBm
Saturated Output Power (Psat)		9			11			11.5		dBm
Output Third Order Intercept (IP3)		16			19			20		dBm
Supply Current (Idd) (Vdd = +3V)		43			43			43		mA



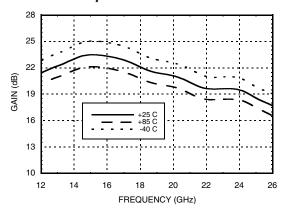


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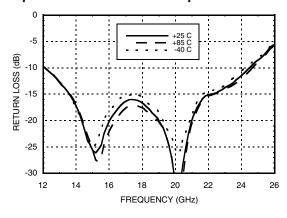
#### **Broadband Gain & Return Loss**



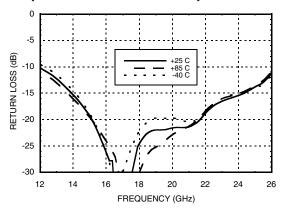
#### Gain vs. Temperature



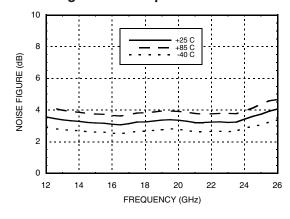
#### Input Return Loss vs. Temperature



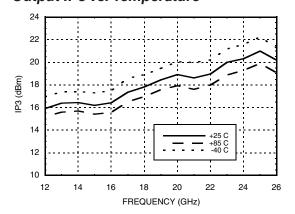
#### **Output Return Loss vs. Temperature**



#### Noise Figure vs. Temperature



## Output IP3 vs. Temperature

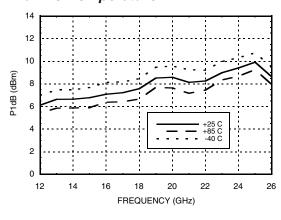




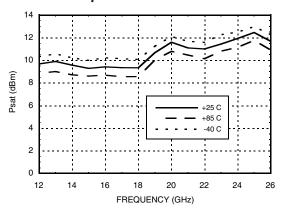


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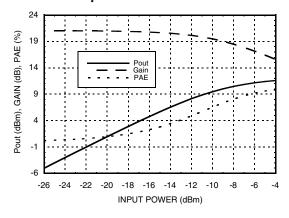
#### P1dB vs. Temperature



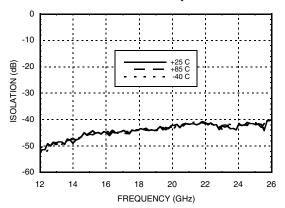
#### Psat vs. Temperature



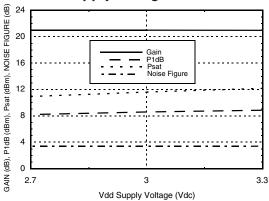
#### Power Compression @ 20 GHz



#### Reverse Isolation vs. Temperature



# Gain, Power & Noise Figure vs. Supply Voltage @ 20 GHz







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#### **Absolute Maximum Ratings**

Drain Bias Voltage (Vdd)	+5.5 Vdc	
RF Input Power (RFIN)(Vdd = +3.0 Vdc)	0 dBm	
Channel Temperature	175 °C	
Continuous Pdiss (T= 85 °C) (derate 3.62 mW/°C above 85 °C)	0.326 W	
Thermal Resistance (channel to ground paddle)	276 °C/W	
Storage Temperature	-65 to +150 °C	
Operating Temperature	-40 to +85 °C	

#### Typical Supply Current vs. Vdd

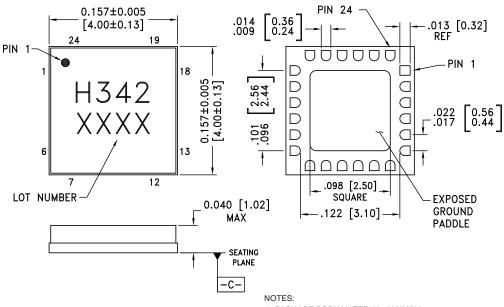
Vdd (Vdc)	ldd (mA)
+2.7	42
+3.0	43
+3.3	44

Note: Amplifier will operate over full voltage ranges shown above.



## **Outline Drawing**

#### **BOTTOM VIEW**



- PACKAGE BODY MATERIAL: ALUMINA.
- 2. LEAD AND GROUND PADDLE PLATING: GOLD FLASH OVER NICKEL.
- 3. DIMENSIONS ARE IN INCHES (MILLIMETERS).
- 4. LEAD SPACING TOLERANCE IS NON-CUMULATIVE.
- 5. PACKAGE WARP SHALL NOT EXCEED 0.05MM DATUM C -
- 6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.

### Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking [2]
HMC342LC4	Alumina, White	Gold over Nickel	MSL3 [1]	H342 XXXX

<sup>[1]</sup> Max peak reflow temperature of 260 °C

<sup>[2] 4-</sup>Digit lot number XXXX





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#### **Pin Descriptions**

Pin Number	Function	Description	Interface Schematic
1, 5 - 14,	N/C No connection required. These pins may be connected to		
18 - 20, 22 - 24	14/0	RF/DC ground without affecting performance.	
2, 4, 15, 17	GND	Package base has an exposed metal ground that must also be connected to RF/DC ground.	○ GND =
3	RFIN	This pin is AC coupled and matched to 50 Ohms.	RFIN ○──
16	RFOUT	This pin is AC coupled and matched to 50 Ohms.	—  —○ RFOUT
21	Vdd	Power Supply Voltage for the amplifier. External bypass capacitors of 100 pF, 1000pF, and 2.2 μF are required.	oVdd ———————————————————————————————————

## **Application Circuit**

Component	Value						
C1	100 pF			Vo	dd		
C2	1,000 pF			(	7		
C3	2.2 µF						
				C1 <u></u>		23=	
				2	.1		
		RFIN	3			16	RFOUT